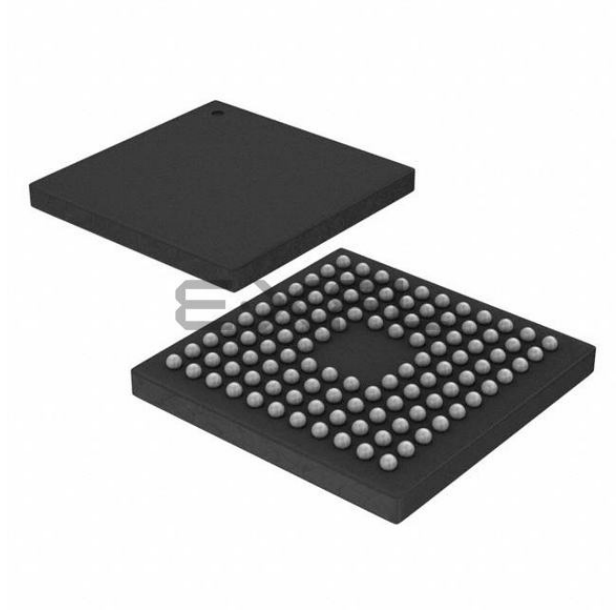

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	90
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	112-LFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg290f128-bga112t

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32WG microcontroller. The flash memory is readable and writable from both the Cortex-M4 and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 µDMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32WG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32WG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32WG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 External Bus Interface (EBI)

The External Bus Interface provides access to external parallel interface devices such as SRAM, FLASH, ADCs and LCDs. The interface is memory mapped into the address bus of the Cortex-M4. This enables seamless access from software without manually manipulating the IO settings each time a read or write is performed. The data and address lines are multiplexed in order to reduce the number of pins required to interface the external devices. The timing is adjustable to meet specifications of the external devices. The interface is limited to asynchronous devices.

2.1.27 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE™), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.28 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG290 to keep track of time and retain data, even if the main power source should drain out.

2.1.29 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.30 General Purpose Input/Output (GPIO)

In the EFM32WG290, there are 90 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32WG290 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1]Based on programmed devices tested for 10000 hours at 150ºC. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		271	286	µA/MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		275		µA/MHz
I_{EM1}	EM1 current (Production test condition = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		63	75	µA/MHz
		48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		65	76	µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		64	75	µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		65	77	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		65	76	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		66	78	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		67	79	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		68	82	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		68	81	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		70	83	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		74	87	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		76	89	µA/MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=25°C		106	120	µA/MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V, T_{AMB}=85°C		112	129	µA/MHz
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=25°C		0.95[1]	1.7[1]	µA

Figure 3.3. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21MHz

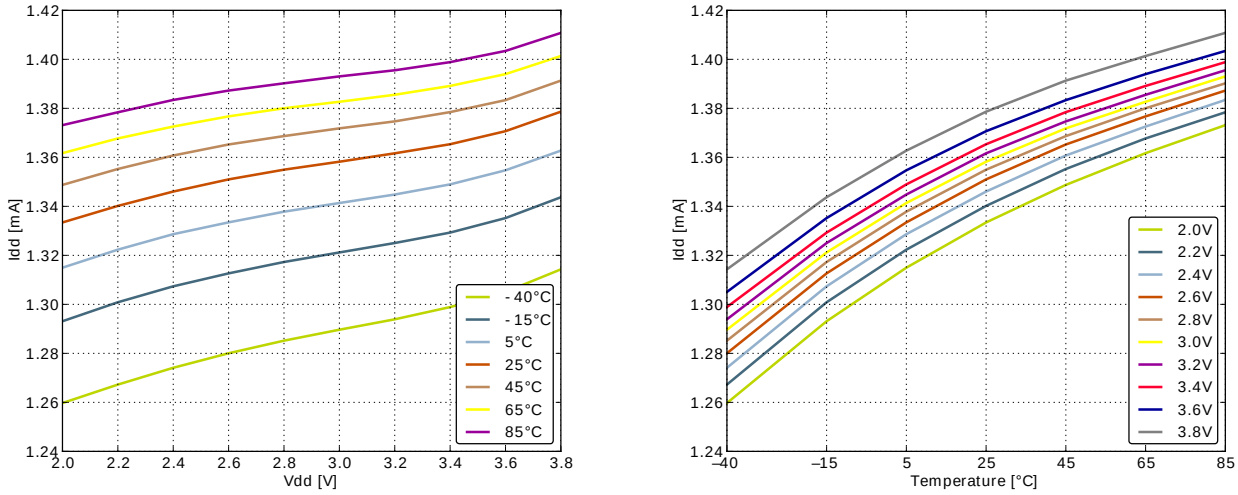


Figure 3.4. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14MHz

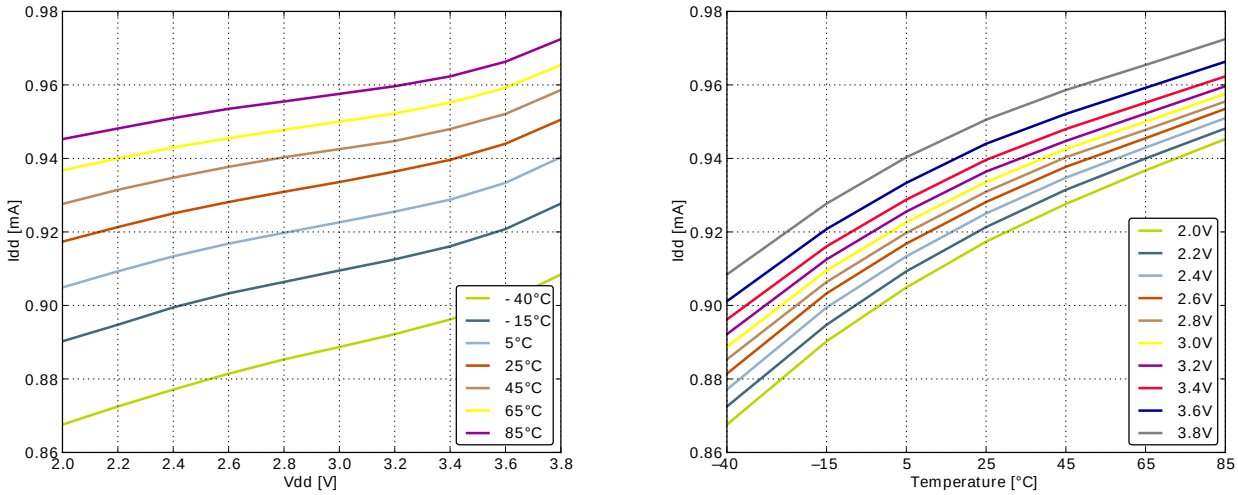
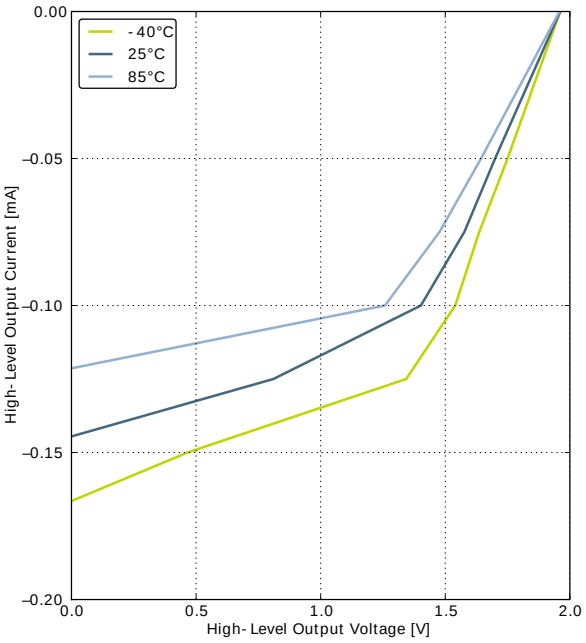
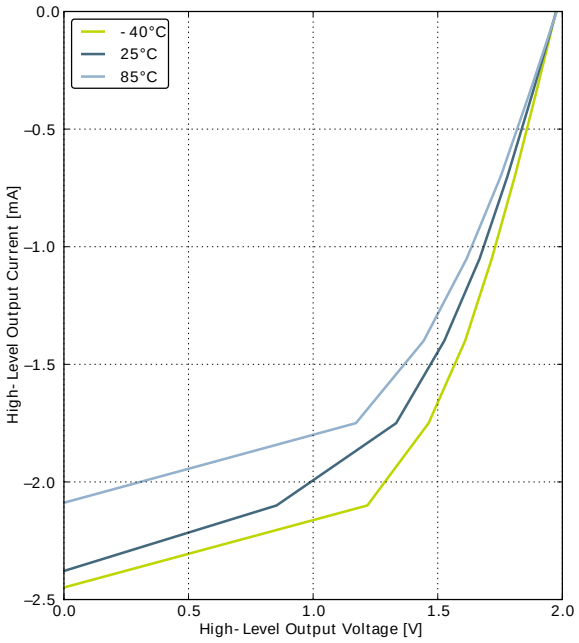


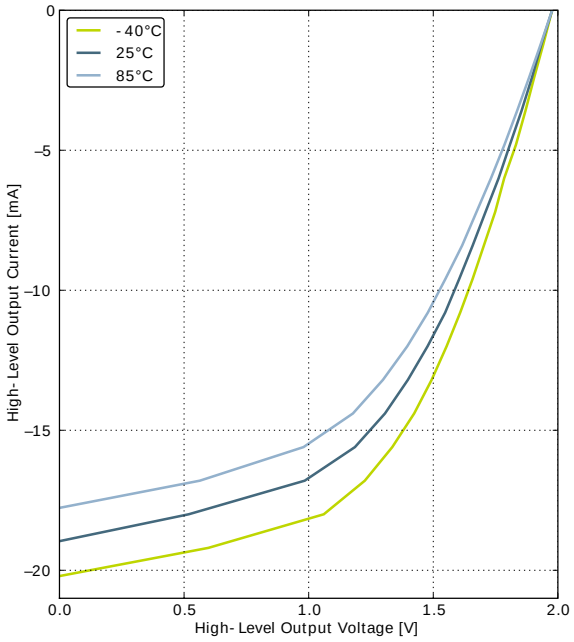
Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage



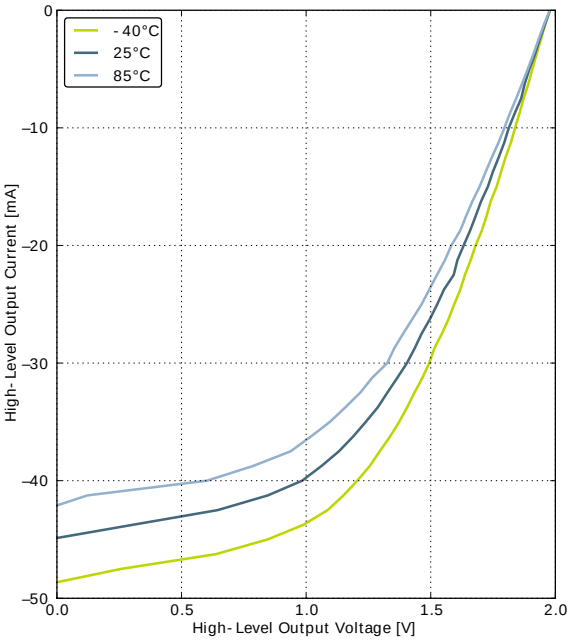
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

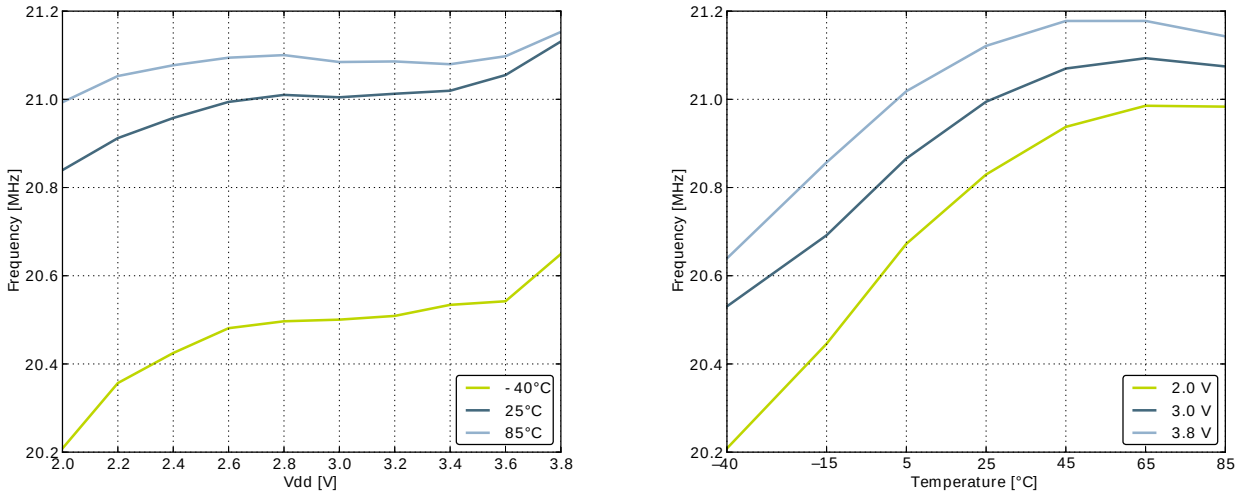
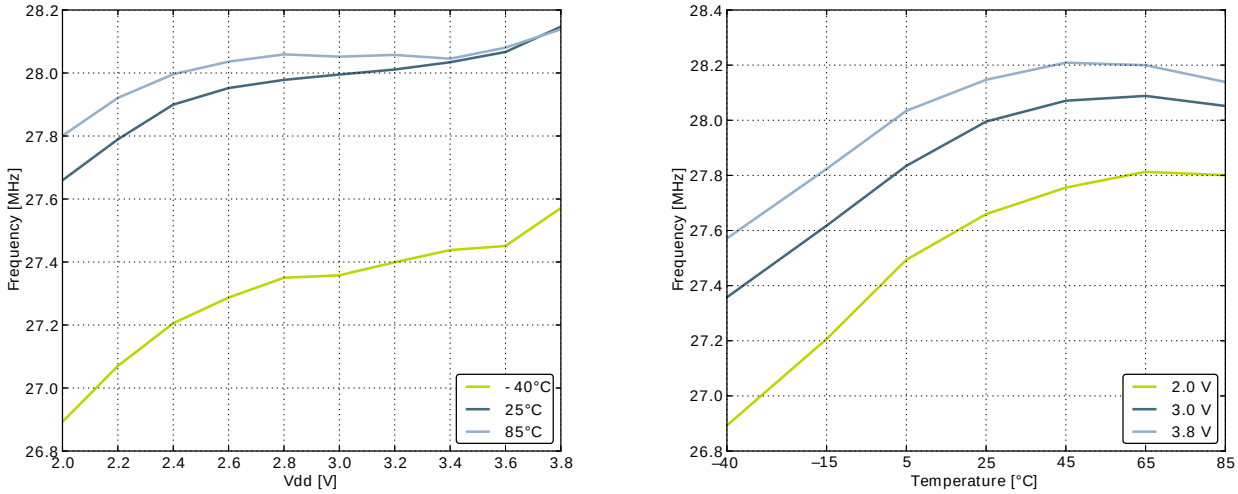


Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
	erence voltage on channel 6					
$V_{ADCCMIN}$	Common mode input range		0		V_{DD}	V
I_{ADCIN}	Input current	2pF sampling capacitors		<100		nA
$CMRR_{ADC}$	Analog input common mode rejection ratio			65		dB
I_{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		µA
I_{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		µA
C_{ADCIN}	Input capacitance			2		pF
R_{ADCIN}	Input ON resistance		1			MOhm
$R_{ADCFILT}$	Input RC filter resistance			10		kOhm
$C_{ADCFILT}$	Input RC filter/decoupling capacitance			250		fF
f_{ADCCLK}	ADC Clock Frequency				13	MHz
$t_{ADCCONV}$	Conversion time	6 bit	7			ADCCLK Cycles
		8 bit	11			ADCCLK Cycles
		12 bit	13			ADCCLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADCCLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator			5		µs

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
$SNDR_{DAC}$	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
$SFDR_{DAC}$	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
$V_{DACOFFSET}$	Offset voltage	After calibration, single ended		2	9	mV
		After calibration, differential		2		mV
DNL_{DAC}	Differential non-linearity			±1		LSB
INL_{DAC}	Integral non-linearity			±5		LSB
MC_{DAC}	No missing codes			12		bits

[1]Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		370	460	µA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	135	µA

Figure 3.40. EBI Read Enable Related Output Timing

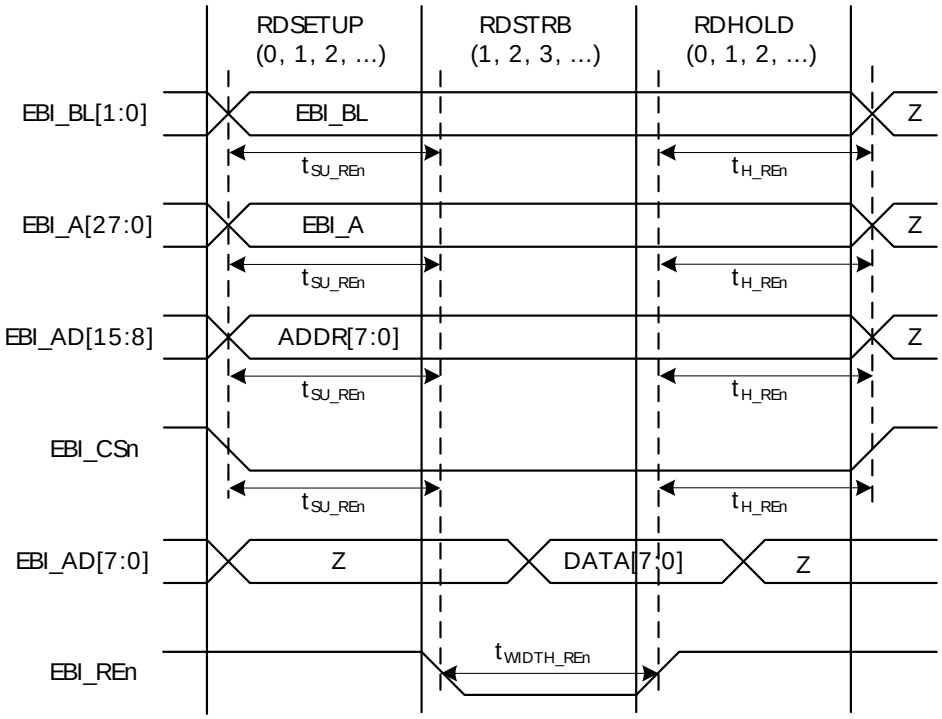


Table 3.22. EBI Read Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_REn} [1 2 3 4]	Output hold time, from trailing EBI_REn/ EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-10.00 + (RDHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_REn} [1 2 3 4 5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_REn/EBI_NANDREn edge	-10.00 + (RDSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_REn} [1 2 3 4 5 6]	EBI_REn pulse width	-9.00 + ((RD-STRB+1) * $t_{HFCORE-CLK}$)			ns

[1]Applies for all addressing modes (figure only shows D8A8. Output timing for EBI_AD only applies to multiplexed addressing modes D8A24ALE and D16A16ALE)

[2]Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

[3]Applies for all polarities (figure only shows active low signals)

[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

[5]The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by 1/2 * $t_{HFCLKNODIV}$.

[6]When page mode is used, RDSTRB is replaced by RDPA for page hits.

Symbol	Parameter	Min	Typ	Max	Unit
t_{H_ARDY} [1 2 3 4]	Hold time, from trailing EBI_REn, EBI_WEn edge to EBI_ARDY invalid	-1 + (3 * $t_{HFCORECLK}$)			ns

[1]Applies for all addressing modes (figure only shows D16A8.)
[2]Applies for EBI_REn, EBI_WEn (figure only shows EBI_REn)
[3]Applies for all polarities (figure only shows active low signals)
[4]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

3.16 I2C

Table 3.25. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and a START condition	4.7			µs

[1]For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32WG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.26. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and a START condition	1.3			µs

[1]For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32WG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.29. SPI Master Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1] [2]	SCLK period		2 * $t_{HFPER-CLK}$			ns
t_{CS_MO} [1] [2]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [1] [2]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [1] [2]	MISO setup time	IOVDD = 3.0 V	-32.00			ns
t_{H_MI} [1] [2]	MISO hold time		63.00			ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

Figure 3.44. SPI Slave Timing

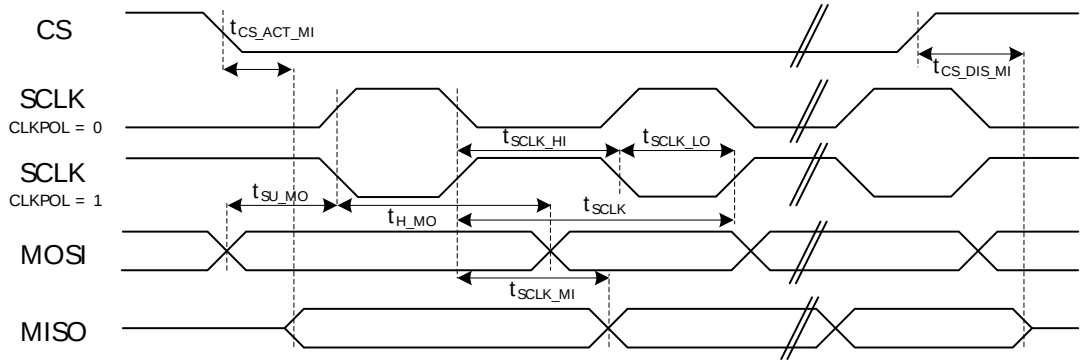


Table 3.30. SPI Slave Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{SCLK_sl} [1] [2]	SCKL period	6 * $t_{HFPER-CLK}$			ns
t_{SCLK_hi} [1] [2]	SCLK high period	3 * $t_{HFPER-CLK}$			ns
t_{SCLK_lo} [1] [2]	SCLK low period	3 * $t_{HFPER-CLK}$			ns
$t_{CS\_ACT\_MI}$ [1] [2]	CS active to MISO	5.00		35.00	ns
$t_{CS\_DIS\_MI}$ [1] [2]	CS disable to MISO	5.00		35.00	ns
t_{SU_MO} [1] [2]	MOSI setup time	5.00			ns
t_{H_MO} [1] [2]	MOSI hold time	2 + 2 * $t_{HF-PERCLK}$			ns
t_{SCLK_MI} [1] [2]	SCLK to MISO	7 + $t_{HFPER-CLK}$		42 + 2 * $t_{HFPERCLK}$	ns

[1]Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)
[2]Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.31. SPI Slave Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Min	Typ	Max	Unit
t_{SCLK_sl} [1] [2]	SCKL period	6 * $t_{HFPER-CLK}$			ns

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32WG290.

4.1 Pinout

The *EFM32WG290* pinout is shown in Figure 4.1 (p. 57) and Table 4.1 (p. 57). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32WG290 Pinout (top view, not to scale)

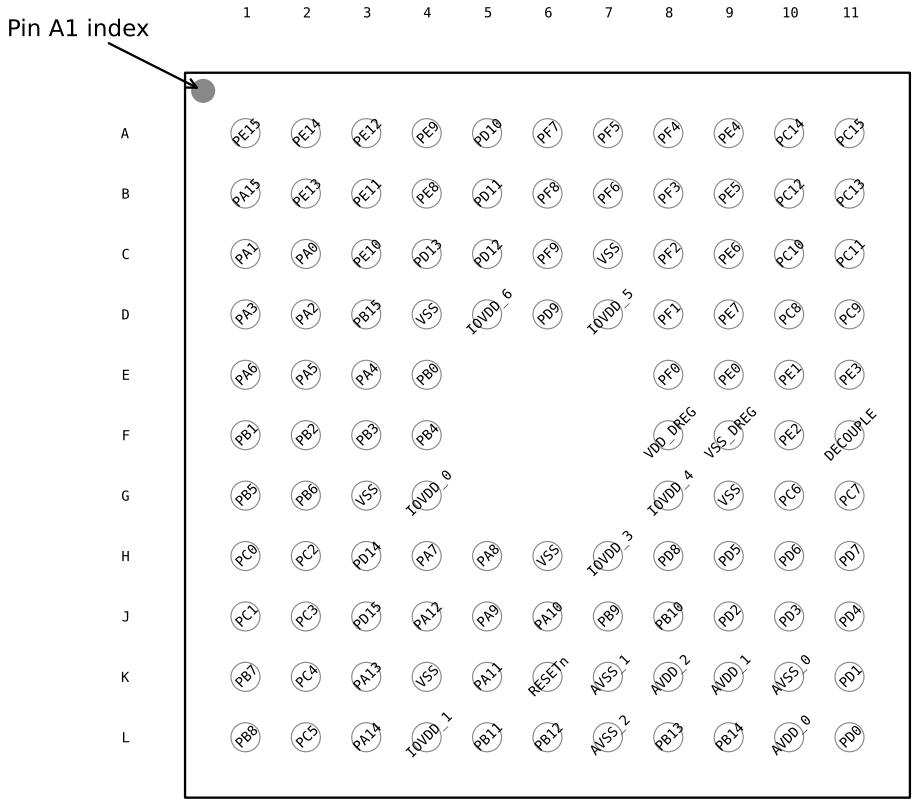


Table 4.1. Device Pinout

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
A1	PE15		EBI_AD07 #0/1/2	TIM3_CC1 #0	LEU0_RX #2	
A2	PE14		EBI_AD06 #0/1/2	TIM3_CC0 #0	LEU0_TX #2	
A3	PE12		EBI_AD04 #0/1/2	TIM1_CC2 #1	US0_RX #3 US0_CLK #0 I2C0_SDA #6	CMU_CLK1 #2 LES_ALTEX6 #0

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
						ETM_TD1 #3
D2	PA2		EBI_AD11 #0/1/2	TIM0_CC2 #0/1		CMU_CLK0 #0 ETM_TD0 #3
D3	PB15					ETM_TD2 #1
D4	VSS	Ground				
D5	IOVDD_6	Digital IO power supply 6.				
D6	PD9		EBI_CS0 #0/1/2			
D7	IOVDD_5	Digital IO power supply 5.				
D8	PF1			TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
D9	PE7		EBI_A14 #0/1/2		US0_TX #1	
D10	PC8	ACMP1_CH0	EBI_A15 #0/1/2	TIM2_CC0 #2	US0_CS #2	LES_CH8 #0
D11	PC9	ACMP1_CH1	EBI_A09 #1/2	TIM2_CC1 #2	US0_CLK #2	LES_CH9 #0 GPIO_EM4WU2
E1	PA6		EBI_AD15 #0/1/2		LEU1_RX #1	ETM_TCLK #3 GPIO_EM4WU1
E2	PA5		EBI_AD14 #0/1/2	TIM0_CDTI2 #0	LEU1_TX #1	LES_ALTEX4 #0 ETM_TD3 #3
E3	PA4		EBI_AD13 #0/1/2	TIM0_CDTI1 #0	U0_RX #2	LES_ALTEX3 #0 ETM_TD2 #3
E4	PB0		EBI_A16 #0/1/2	TIM1_CC0 #2		
E8	PF0			TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1/2/3
E9	PE0		EBI_A07 #0/1/2	TIM3_CC0 #1 PCNT0_S0IN #1	U0_TX #1 I2C1_SDA #2	
E10	PE1		EBI_A08 #0/1/2	TIM3_CC1 #1 PCNT0_S1IN #1	U0_RX #1 I2C1_SCL #2	
E11	PE3	BU_STAT	EBI_A10 #0		U1_RX #3	ACMP1_O #1
F1	PB1		EBI_A17 #0/1/2	TIM1_CC1 #2		
F2	PB2		EBI_A18 #0/1/2	TIM1_CC2 #2		
F3	PB3		EBI_A19 #0/1/2	PCNT1_S0IN #1	US2_TX #1	
F4	PB4		EBI_A20 #0/1/2	PCNT1_S1IN #1	US2_RX #1	
F8	VDD_DREG	Power supply for on-chip voltage regulator.				
F9	VSS_DREG	Ground for on-chip voltage regulator.				
F10	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1
F11	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size $C_{DECOUPLE}$ is required at this pin.				
G1	PB5		EBI_A21 #0/1/2		US2_CLK #1	
G2	PB6		EBI_A22 #0/1/2		US2_CS #1	
G3	VSS	Ground				
G4	IOVDD_0	Digital IO power supply 0.				
G8	IOVDD_4	Digital IO power supply 4.				
G9	VSS	Ground				
G10	PC6	ACMP0_CH6	EBI_A05 #0/1/2		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
EBI_AD01	PE9	PE9	PE9					External Bus Interface (EBI) address and data input / output pin 01.
EBI_AD02	PE10	PE10	PE10					External Bus Interface (EBI) address and data input / output pin 02.
EBI_AD03	PE11	PE11	PE11					External Bus Interface (EBI) address and data input / output pin 03.
EBI_AD04	PE12	PE12	PE12					External Bus Interface (EBI) address and data input / output pin 04.
EBI_AD05	PE13	PE13	PE13					External Bus Interface (EBI) address and data input / output pin 05.
EBI_AD06	PE14	PE14	PE14					External Bus Interface (EBI) address and data input / output pin 06.
EBI_AD07	PE15	PE15	PE15					External Bus Interface (EBI) address and data input / output pin 07.
EBI_AD08	PA15	PA15	PA15					External Bus Interface (EBI) address and data input / output pin 08.
EBI_AD09	PA0	PA0	PA0					External Bus Interface (EBI) address and data input / output pin 09.
EBI_AD10	PA1	PA1	PA1					External Bus Interface (EBI) address and data input / output pin 10.
EBI_AD11	PA2	PA2	PA2					External Bus Interface (EBI) address and data input / output pin 11.
EBI_AD12	PA3	PA3	PA3					External Bus Interface (EBI) address and data input / output pin 12.
EBI_AD13	PA4	PA4	PA4					External Bus Interface (EBI) address and data input / output pin 13.
EBI_AD14	PA5	PA5	PA5					External Bus Interface (EBI) address and data input / output pin 14.
EBI_AD15	PA6	PA6	PA6					External Bus Interface (EBI) address and data input / output pin 15.
EBI_ALE	PF3	PC11	PC11					External Bus Interface (EBI) Address Latch Enable output.
EBI_ARDY	PF2	PF2	PF2					External Bus Interface (EBI) Hardware Ready Control input.
EBI_BL0	PF6	PF6	PF6					External Bus Interface (EBI) Byte Lane/Enable pin 0.
EBI_BL1	PF7	PF7	PF7					External Bus Interface (EBI) Byte Lane/Enable pin 1.
EBI_CS0	PD9	PD9	PD9					External Bus Interface (EBI) Chip Select output 0.
EBI_CS1	PD10	PD10	PD10					External Bus Interface (EBI) Chip Select output 1.
EBI_CS2	PD11	PD11	PD11					External Bus Interface (EBI) Chip Select output 2.
EBI_CS3	PD12	PD12	PD12					External Bus Interface (EBI) Chip Select output 3.
EBI_CSTFT	PA7	PA7	PA7					External Bus Interface (EBI) Chip Select output TFT.
EBI_DCLK	PA8	PA8	PA8					External Bus Interface (EBI) TFT Dot Clock pin.
EBI_DTEN	PA9	PA9	PA9					External Bus Interface (EBI) TFT Data Enable pin.
EBI_HSNC	PA11	PA11	PA11					External Bus Interface (EBI) TFT Horizontal Synchronization pin.
EBI_NANDREn	PC3	PC3	PC3					External Bus Interface (EBI) NAND Read Enable output.
EBI_NANDWEn	PC5	PC5	PC5					External Bus Interface (EBI) NAND Write Enable output.
EBI_REn	PF5	PF9	PF5					External Bus Interface (EBI) Read Enable output.
EBI_VSNC	PA10	PA10	PA10					External Bus Interface (EBI) TFT Vertical Synchronization pin.
EBI_WEn	PF4	PF8	PF4					External Bus Interface (EBI) Write Enable output.
ETM_TCLK	PD7	PF8	PC6	PA6				Embedded Trace Module ETM clock .

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
ETM_TD0	PD6	PF9	PC7	PA2				Embedded Trace Module ETM data 0.
ETM_TD1	PD3	PD13	PD3	PA3				Embedded Trace Module ETM data 1.
ETM_TD2	PD4	PB15	PD4	PA4				Embedded Trace Module ETM data 2.
ETM_TD3	PD5	PF3	PD5	PA5				Embedded Trace Module ETM data 3.
GPIO_EM4WU0	PA0							Pin can be used to wake the system up from EM4
GPIO_EM4WU1	PA6							Pin can be used to wake the system up from EM4
GPIO_EM4WU2	PC9							Pin can be used to wake the system up from EM4
GPIO_EM4WU3	PF1							Pin can be used to wake the system up from EM4
GPIO_EM4WU4	PF2							Pin can be used to wake the system up from EM4
GPIO_EM4WU5	PE13							Pin can be used to wake the system up from EM4
HFXTAL_N	PB14							High Frequency Crystal negative pin. Also used as external optional clock input pin.
HFXTAL_P	PB13							High Frequency Crystal positive pin.
I2C0_SCL	PA1	PD7	PC7	PD15	PC1	PF1	PE13	I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6	PC6	PD14	PC0	PF0	PE12	I2C0 Serial Data input / output.
I2C1_SCL	PC5	PB12	PE1					I2C1 Serial Clock Line input / output.
I2C1_SDA	PC4	PB11	PE0					I2C1 Serial Data input / output.
LES_ALTEX0	PD6							LESENSE alternate exite output 0.
LES_ALTEX1	PD7							LESENSE alternate exite output 1.
LES_ALTEX2	PA3							LESENSE alternate exite output 2.
LES_ALTEX3	PA4							LESENSE alternate exite output 3.
LES_ALTEX4	PA5							LESENSE alternate exite output 4.
LES_ALTEX5	PE11							LESENSE alternate exite output 5.
LES_ALTEX6	PE12							LESENSE alternate exite output 6.
LES_ALTEX7	PE13							LESENSE alternate exite output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH2	PC2							LESENSE channel 2.
LES_CH3	PC3							LESENSE channel 3.
LES_CH4	PC4							LESENSE channel 4.
LES_CH5	PC5							LESENSE channel 5.
LES_CH6	PC6							LESENSE channel 6.
LES_CH7	PC7							LESENSE channel 7.
LES_CH8	PC8							LESENSE channel 8.
LES_CH9	PC9							LESENSE channel 9.
LES_CH10	PC10							LESENSE channel 10.
LES_CH11	PC11							LESENSE channel 11.
LES_CH12	PC12							LESENSE channel 12.
LES_CH13	PC13							LESENSE channel 13.
LES_CH14	PC14							LESENSE channel 14.
LES_CH15	PC15							LESENSE channel 15.
LETIM0_OUT0	PD6	PB11	PF0	PC4				Low Energy Timer LETIM0, output channel 0.

Figure 5.2. BGA112 PCB Solder Mask

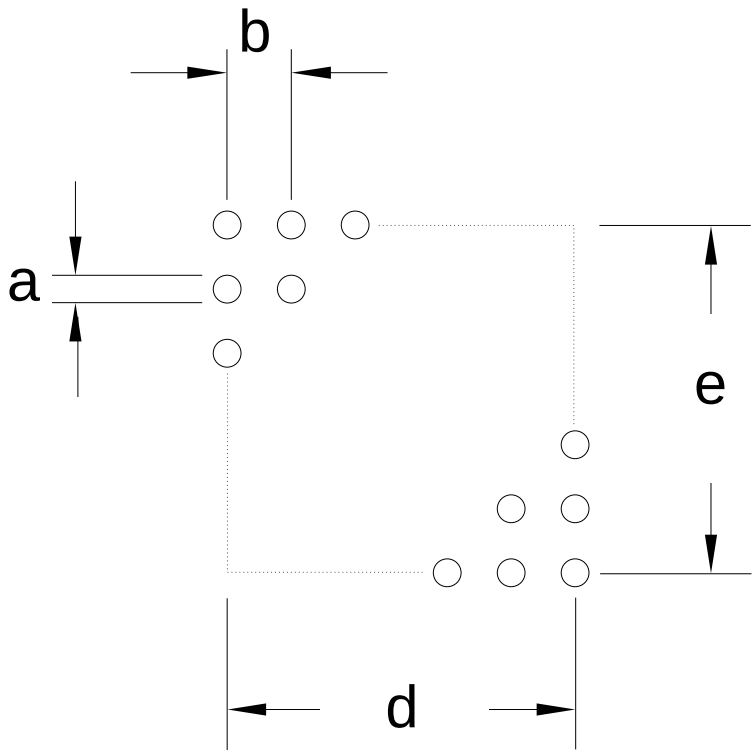


Table 5.2. BGA112 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.48
b	0.80
d	8.00
e	8.00

7 Revision History

7.1 Revision 1.40

June 13th, 2014

Removed "Preliminary" markings.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Added AUXHFRCO to blockdiagram and electrical characteristics.

Updated current consumption data.

Updated transition between energy modes data.

Updated power management data.

Updated GPIO data.

Updated LFRCO, HFRCO and ULFRCO data.

Updated ADC data.

Updated DAC data.

Updated OPAMP data.

Updated ACMP data.

Updated VCMP data.

Added EBI timing chapter.

7.2 Revision 1.31

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.3 Revision 1.30

September 30th, 2013

Added I2C characterization data.

Added SPI characterization data.

Corrected the DAC and OPAMP2 pin sharing information in the Alternate Functionality Pinout section.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Updated the EM0 and EM1 current consumption numbers. Updated the the EM1 plots and removed the EM0 plots.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.4 Revision 1.20

June 28th, 2013

Updated PCB Land Pattern, PCB Solder Mask and PCB Stencil Design figures.

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.5 Revision 1.10

May 6th, 2013

Updated current consumption table and figures in Electrical characteristics section.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Corrected BGA solder balls material from Sn96.5/Ag3/Cu0.5 to SAC105.

Other minor corrections.

7.7 Revision 0.95

May 3rd, 2012

Updated EM2/EM3 current consumption at 85°C.

7.8 Revision 0.90

February 27th, 2012

Initial preliminary release.

silabs.com


ZERO
ARM Cortex-M0+
TINY
ARM Cortex-M3
GECKO
ARM Cortex-M3
LEOPARD
ARM Cortex-M3
GIANT
ARM Cortex-M3
WONDER
ARM Cortex-M4